



Atty. Docket No. 8022-1003

PATENTS

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Takuya KITAMURA

Confirmation No. 3547

Serial No. 10/068,893

GROUP 2823

Filed February 11, 2002

Examiner Suk San Foong

SEMICONDUCTOR MEMORY DEVICE FOR
INCREASING ACCESS SPEED THEREOF

AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Responsive to the Official Action of February 10, 2003,
please amend the above-identified application as follows:

IN THE SPECIFICATION:

Page 20, replace the paragraph, beginning on line 25,
bridging pages 20 and 21, as follows:

--As shown in Fig. 2, the inter-level dielectric 16 is
covered with a silicon oxynitride film 21 and an inter-level
dielectric 22. The inter-level dielectric 22 is formed of
silicon oxide deposited by a plasma CVD (chemical vapor
deposition) method. The silicon oxynitride film 21 is an etching
stopper for etching of the inter-level dielectric 22.--

IN THE CLAIMS:

Cancel claim 1.

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